



Lead (Pb) Free Product RoHS compliant

# PD1300-130D32-I InGaAs PIN-PD

PD1300-130D32-I is InGaAs PIN-photodiode featuring excellent responsibility and high photocurrent for near infrared.

This PIN-photodiode consists of a large chip with Φ1mm dia. of active area mounted on the TO-18 stem and is hermetical sealed by metal can with glass ball lens.

These devices are designed to be high photocurrent gains with angle of half sensitivity of ±18degrees.

◆ Features

- 1) High Current
- 2) High Response

◆ Specifications

- 1) Product Name InGaAs PIN Photo-Diode
- 2) Type No. PD1300-130D32-I
- 3) Chip
  - (1) Active Area Φ1mm dia
- 4) Package
  - (1) Type TO-18 (3pins)
  - (2) Lens Glass Ball Lens
  - (2) Cap Gold Plated

◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	V <sub>BD</sub>	20	V
Operating Temperature	T <sub>OPR</sub>	-40 ~ +90	°C
Storage Temperature	T <sub>STG</sub>	-40 ~ +125	°C
Soldering Temperature	T <sub>SOL</sub>	265	°C

‡Pulse Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics [25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	unit
Photo Responsivity	R <sub>E</sub>	V <sub>R</sub> =3V, λ <sub>P</sub> =1300nm		0.9		A/W
Photo Current	I <sub>L</sub>	V <sub>R</sub> =3V, λ <sub>P</sub> =1300nm	160			uA(±1)
Dark Current	I <sub>D</sub>	V <sub>R</sub> =3V		2	20	nA
Spectral Responsivity	λ <sub>P</sub>	V <sub>R</sub> =3V	1000		1550	nm
Half Angle of Sensitivity	θ <sub>1/2</sub>	V <sub>R</sub> =0V		±15		deg.
Total Capacitance	C <sub>T</sub>	f=1MHz, V <sub>R</sub> =0V		200		pF

◆ Outer dimension (Unit: mm)

